

iscN-Channel MOSFET Transistor

IRFIB7N50A

• FEATURES

- Low drain-source on-resistance: R_Ds(ON) =0.52Ω (MAX)
- · Enhancement mode:
 - Vth = 2.0 to 4.0V (VDs = 10 V, ID=0.25mA)
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

DESCRITION

Switching Voltage Regulators

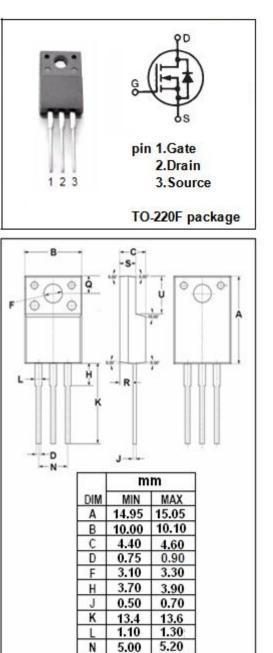
• ABSOLUTE MAXIMUM RATINGS(Ta=25°C)

SYMBOL	PARAMETER	VALUE	UNIT	
V _{DSS}	Drain-Source Voltage 500		V	
V _{GS}	Gate-Source Voltage	ate-Source Voltage ±30		
ID	Drain Current-Continuous 6.6		A	
I _{DM}	Drain Current-Single Pulsed 44		A	
P _D	Total Dissipation @T _c =25℃	60	W	
Tj	Max. Operating Junction Temperature	-55~150	°C	
T _{stg}	Storage Temperature	-55~150	°C	
	1	1		

• THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	МАХ	UNIT
Rth(ch-c)	Channel-to-case thermal resistance	2.1	°C/W

1



2.90

2.40

2.90

6.60

0

R

S

11

2.70 2.20

2.65

6.40



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ELECTRICAL CHARACTERISTICS

$T_{\texttt{C}}\text{=}25^{\circ}\!\!\!\mathbb{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	ТҮР	МАХ	UNIT
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V; I _D = 0.25mA	500			V
V _{GS} (th)	Gate Threshold Voltage	V _{DS} = 10V; I _D =0.25mA	2.0		4.0	V
R _{DS(on)}	Drain-Source On-Resistance	V _{GS} =10V; I _D =4.0A			0.52	Ω
lgss	Gate-Source Leakage Current	V _{GS} = ±30V;V _{DS} = 0V			±100	nA
I _{DSS}	Drain-Source Leakage Current	V _{DS} =500V; V _{GS} = 0V V _{DS} =400V; V _{GS} = 0V;T _J =125°C			25 250	μA
V _{SDF}	Diode forward voltage	I _{DR} =11A, V _{GS} = 0 V			1.5	V

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